

electrically connecting electrodes of the semiconductor device to the leads;
and
cutting the substrate while leaving uncut at least one of the conduction sections connected to a corresponding lead.--

--21. The method of claim 20, wherein the semiconductor device includes a surface having the electrodes, the surface of the semiconductor device is attached to the substrate, and the electrodes of the semiconductor device are directly connected to the leads.--

Q' --22. The method of claim 21, further comprising a step of providing conductive connection member at the electrodes of the semiconductor device, wherein the step of electrically connecting the electrodes and the leads includes a step of providing insulation adhesive members between the electrodes and the leads, a step of pushing the semiconductor device against the substrate and heating the semiconductor device and the substrate at a temperature higher than a melting temperature of the insulation adhesive member and lower than a melting temperature of the conductive connection member, and a step of melting the conductive connection member.--

--23. The method of claim 19, wherein the substrate is provided with a through-hole for each of the leads, the through-holes communicate with leads on the side of a central area of the substrate, and wherein the conduction sections are electrically connected to corresponding ones of the leads through the through-hole of the substrate and the substrate is cut after the step for electrically connecting the electrodes and the leads.--

--24. The method of claim 19, wherein the substrate is provided with a plurality of through-holes for each of the leads, the through-holes communicate with the leads, the conduction sections are electrically connected to corresponding ones of the leads through

predetermined ones of the through-holes, and the substrate is cut after the step for electrically connecting the electrodes and the leads.--

ai --25. The method of claim 19, wherein the substrate is provided with a plurality of through-holes for each one of the leads, internal surfaces of the through-holes are made to be conductive and connected to the corresponding one of the leads, and the substrate is cut at locations that pass predetermined ones of the through-holes to define the conduction sections.--

REMARKS

Claims 1-12 and 19-25 are pending. By this Response, claims 13-18 are canceled, claims 19-25 are added and Group I, claims 1-12, are elected, with traverse.

It is respectfully submitted that the method as recited in new claim 19 (and claims 20-25 dependent therefrom) recites a method of manufacturing of a semiconductor apparatus that is not restrictable from elected claim 1. In particular, new method claim 19 contains all the limitations of claim 1 and cannot be used to make other and different products from claim 1, and the semiconductor apparatus according to claim 1 cannot be made by another and materially different method from that recited in claim 19. Accordingly, claims 19-25 are not distinct inventions from claims 1-12 under MPEP §806.05(f).

Further, as required in MPEP §821.04, if Applicants elect claims directed to a product, and a product claim is subsequently found allowable, withdrawn process claims which include all the limitations of an allowable product claim will be rejoined. In summary, the claims of the application are not properly restrictable, and even if they were, rejoinder will ultimately be required.

Should the Examiner have any questions regarding this matter, the Examiner is invited to contact Applicant undersigned attorney at the telephone number listed below.

Respectfully submitted,


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